

# NPN 2N3773\*, PNP 2N6609

Preferred Device

## Complementary Silicon Power Transistors

The 2N3773 and 2N6609 are PowerBase™ power transistors designed for high power audio, disk head positioners and other linear applications. These devices can also be used in power switching circuits such as relay or solenoid drivers, DC–DC converters or inverters.

### Features

- Pb–Free Packages are Available\*\*
- High Safe Operating Area (100% Tested) 150 W @ 100 V
- Completely Characterized for Linear Operation
- High DC Current Gain and Low Saturation Voltage  
 $h_{FE} = 15$  (Min) @ 8.0 A, 4.0 V  
 $V_{CE(sat)} = 1.4$  V (Max) @  $I_C = 8.0$  A,  $I_B = 0.8$  A
- For Low Distortion Complementary Designs

### MAXIMUM RATINGS (Note 1)

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	$V_{CEO}$	140	Vdc
Collector – Emitter Voltage	$V_{CEX}$	160	Vdc
Collector – Base Voltage	$V_{CBO}$	160	Vdc
Emitter – Base Voltage	$V_{EBO}$	7	Vdc
Collector Current	$I_C$		Adc
– Continuous		16	
– Peak (Note 2)		30	
Base Current	$I_B$		Adc
– Continuous		4	
– Peak (Note 2)		15	
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	150 0.855	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	–65 to +200	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Indicates JEDEC Registered Data.
2. Pulse Test: Pulse Width = 5 ms, Duty Cycle  $\leq$  10%.

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	1.17	$^\circ\text{C}/\text{W}$

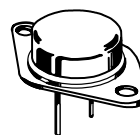
\*\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



ON Semiconductor®

## 16 A COMPLEMENTARY POWER TRANSISTORS 140 V, 150 W

### MARKING DIAGRAM



TO–204  
CASE 1–07



xxxx = 3773 or 6609  
 A = Assembly Location  
 YY = Year  
 WW = Work Week

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

\*Preferred devices are recommended choices for future use and best overall value.

# NPN 2N3773\*, PNP 2N6609

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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### OFF CHARACTERISTICS (Note 3)

Collector–Emitter Breakdown Voltage (Note 4) (I <sub>C</sub> = 0.2 Adc, I <sub>B</sub> = 0)	V <sub>CEO(sus)</sub>	140	–	Vdc
Collector–Emitter Sustaining Voltage (Note 4) (I <sub>C</sub> = 0.1 Adc, V <sub>BE(off)</sub> = 1.5 Vdc, R <sub>BE</sub> = 100 Ohms)	V <sub>CEX(sus)</sub>	160	–	Vdc
Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 0.2 Adc, R <sub>BE</sub> = 100 Ohms)	V <sub>CER(sus)</sub>	150	–	Vdc
Collector Cutoff Current (Note 4) (V <sub>CE</sub> = 120 Vdc, I <sub>B</sub> = 0)	I <sub>CEO</sub>	–	10	mAdc
Collector Cutoff Current (Note 4) (V <sub>CE</sub> = 140 Vdc, V <sub>BE(off)</sub> = 1.5 Vdc) (V <sub>CE</sub> = 140 Vdc, V <sub>BE(off)</sub> = 1.5 Vdc, T <sub>C</sub> = 150°C)	I <sub>CEX</sub>	– –	2 10	mAdc
Collector Cutoff Current (V <sub>CB</sub> = 140 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	–	2	mAdc
Emitter Cutoff Current (Note 4) (V <sub>BE</sub> = 7 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	–	5	mAdc

### ON CHARACTERISTICS (Note 3)

DC Current Gain (I <sub>C</sub> = 8 Adc, V <sub>CE</sub> = 4 Vdc) (Note 4) (I <sub>C</sub> = 16 Adc, V <sub>CE</sub> = 4 Vdc)	h <sub>FE</sub>	15 5	60 –	–
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 8 Adc, I <sub>B</sub> = 800 mAdc) (Note 4) (I <sub>C</sub> = 16 Adc, I <sub>B</sub> = 3.2 Adc)	V <sub>CE(sat)</sub>	– –	1.4 4	Vdc
Base–Emitter On Voltage (Note 4) (I <sub>C</sub> = 8 Adc, V <sub>CE</sub> = 4 Vdc)	V <sub>BE(on)</sub>	–	2.2	Vdc

### DYNAMIC CHARACTERISTICS

Magnitude of Common–Emitter Small–Signal, Short–Circuit, Forward Current Transfer Ratio (I <sub>C</sub> = 1 A, f = 50 kHz)	h <sub>fe</sub>	4	–	–
Small–Signal Current Gain (Note 4) (I <sub>C</sub> = 1 Adc, V <sub>CE</sub> = 4 Vdc, f = 1 kHz)	h <sub>fe</sub>	40	–	–

### SECOND BREAKDOWN CHARACTERISTICS

Second Breakdown Collector Current with Base Forward Biased t = 1 s (non–repetitive), V <sub>CE</sub> = 100 V, See Figure 12	I <sub>S/b</sub>	1.5	–	Adc
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3. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

4. Indicates JEDEC Registered Data.

### ORDERING INFORMATION

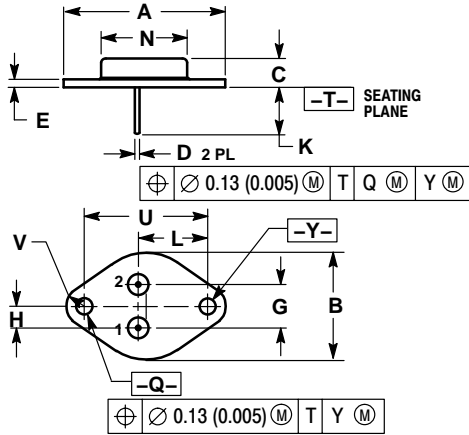
Device	Package	Shipping <sup>†</sup>
2N3773	TO–204	100 Unit / Tray
2N3773G	TO–204 (Pb–Free)	100 Unit / Tray
2N6609	TO–204	100 Unit / Tray

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NPN 2N3773\*, PNP 2N6609

## PACKAGE DIMENSIONS

TO-204 (TO-3)  
CASE 1-07  
ISSUE Z



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.550 REF		39.37 REF	
B	---	1.050	---	26.67
C	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
E	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	---	0.830	---	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

STYLE 1:

1. BASE
  2. EMITTER
- CASE: COLLECTOR